

FIG. 1

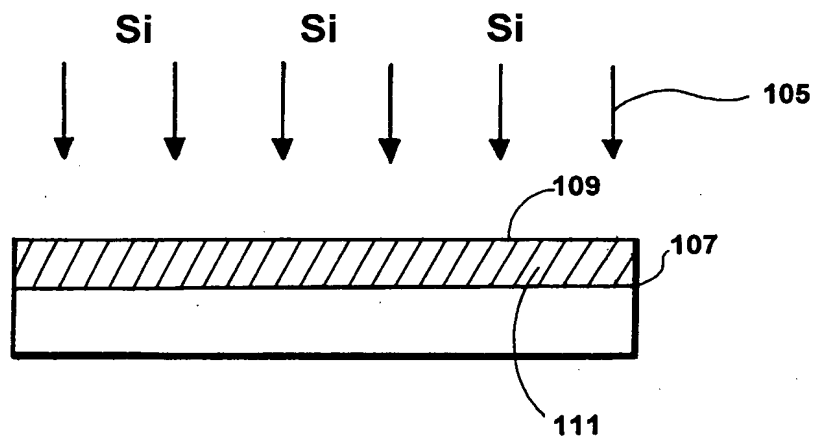


FIG. 2

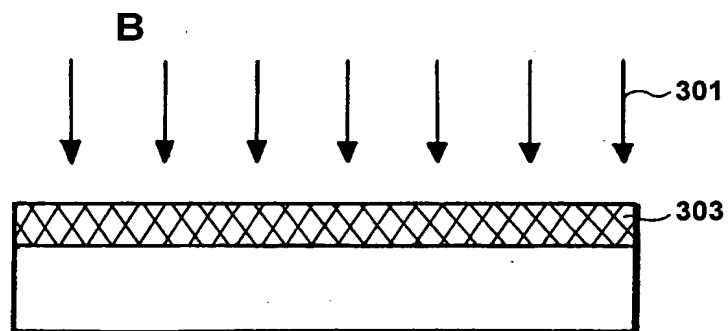


FIG. 3

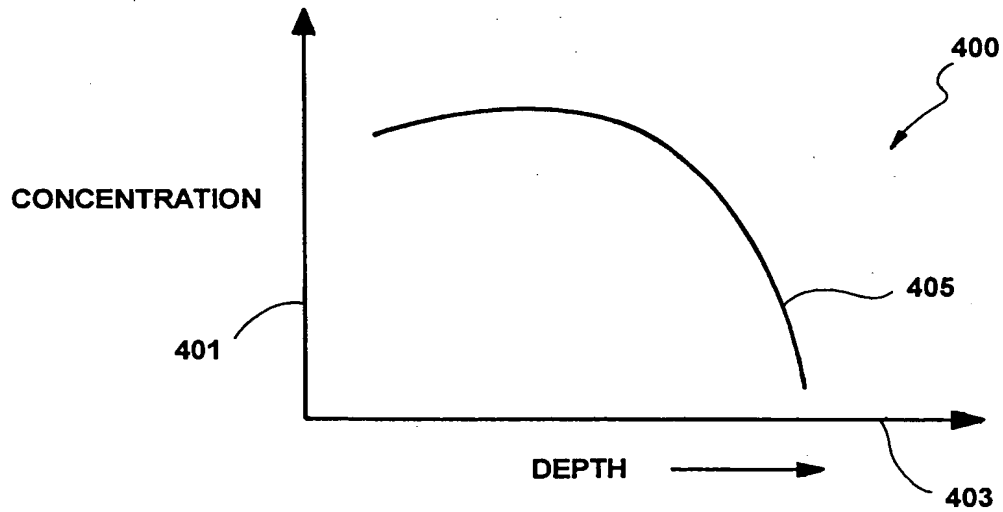


FIG. 4

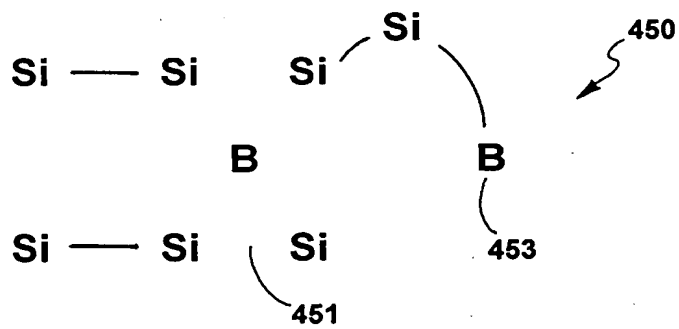


FIG. 4A

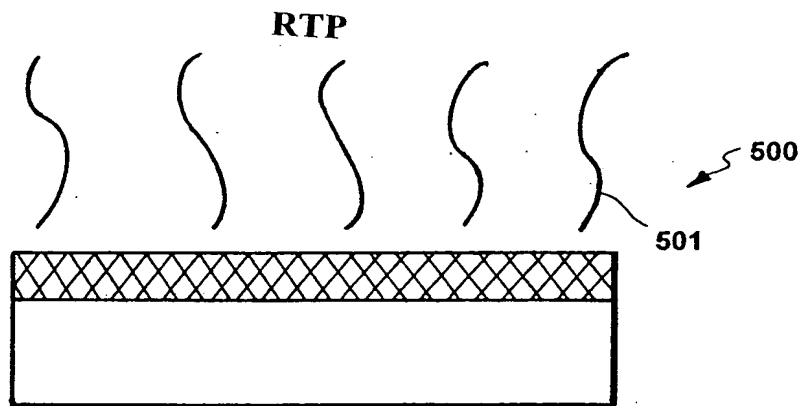


FIG. 5

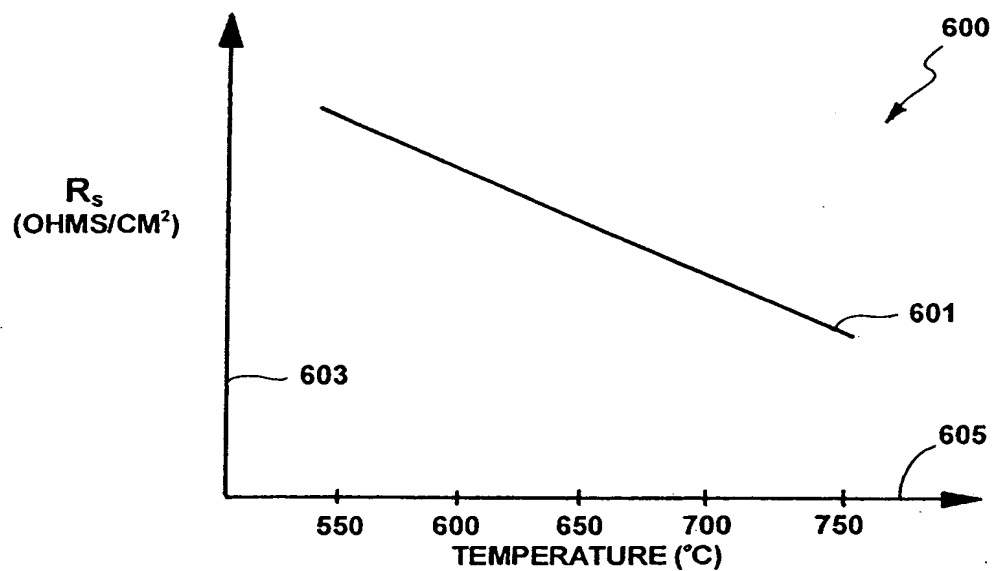


FIG. 6

Low temperature monitor

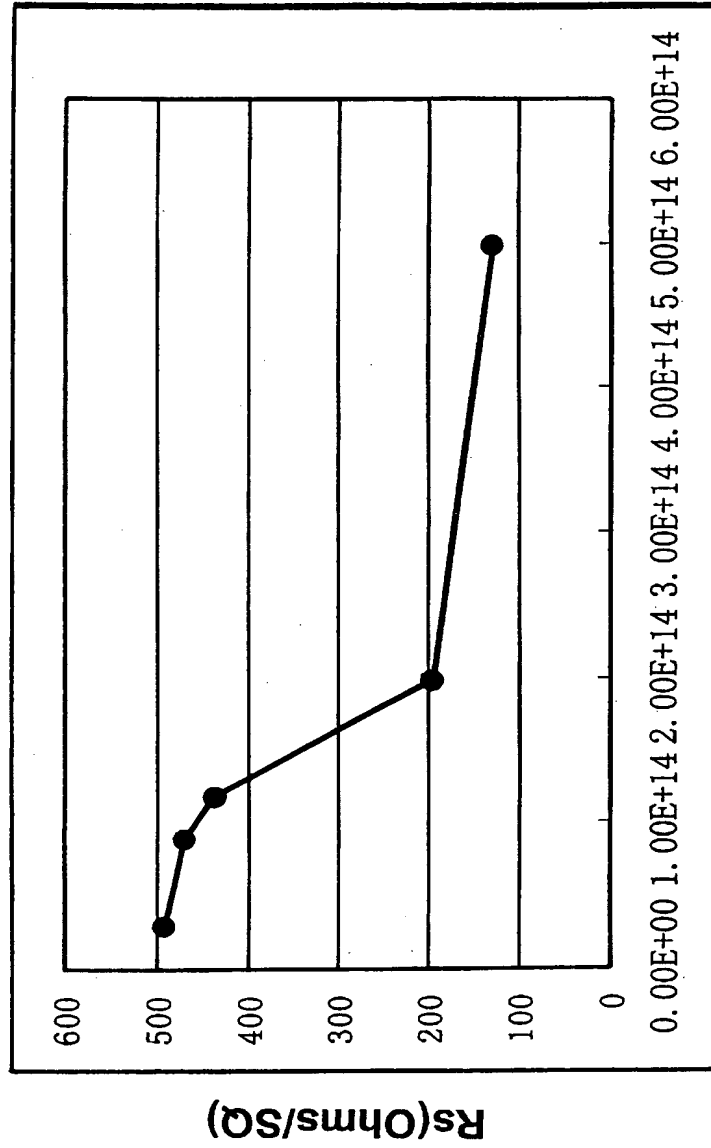


Figure 7: Changes of Rs as a function of implant dosage of silicon,
Boron dosage unchanged(3.5E15).

FIG. 7

Low temperature monitor

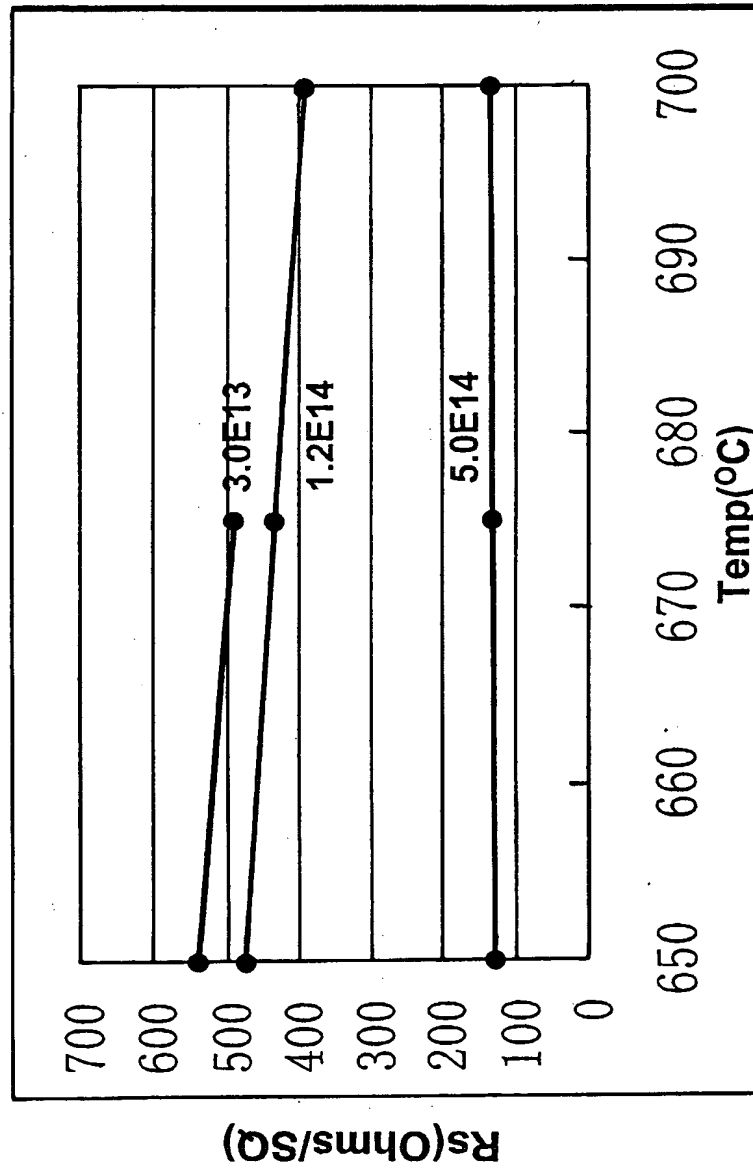


Figure 8: The dependence of R_s on annealing temperature. The implant dose of silicon varied from $3.0E13$ to $5.0E14$, Boron dosage unchanged ($3.5E15$).

FIG. 8